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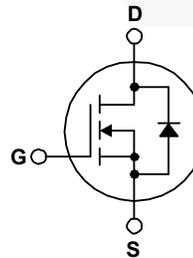
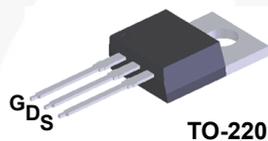
N-Channel UniFET™ MOSFET 60 V, 80 A, 10 mΩ

Features

- $R_{DS(on)} = 8.5 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 40 \text{ A}$
- Low Gate Charge (Typ. 57nC)
- Low C_{rss} (Typ. 145pF)
- Fast Switching
- Improved dv/dt Capability
- RoHS Compliant

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	60	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	80
		- Continuous ($T_C = 100^\circ\text{C}$)	65
I_{DM}	Drain Current	- Pulsed (Note 1)	320
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	480
I_{AR}	Avalanche Current	(Note 1)	80
E_{AR}	Repetitive Avalanche Energy	(Note 1)	17.6
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	176
		- Derate above 25°C	1.17
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.85	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP80N06	FDP80N06	TO-220	Tube	N/A	50 units

Electrical Characteristics

TC = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A, V_{GS} = 0V, T_J = 25^\circ C$	60	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A, \text{Referenced to } 25^\circ C$	-	0.075	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, T_C = 150^\circ C$	-	-	1 10	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 40A$	-	8.5	10	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 25V, I_D = 40A$	-	67	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1MHz$	-	2450	3190	pF
C_{oss}	Output Capacitance		-	910	1190	pF
C_{rss}	Reverse Transfer Capacitance		-	145	190	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30V, I_D = 80A$ $R_G = 25\Omega$	-	32	75	ns
t_r	Turn-On Rise Time		-	259	528	ns
$t_{d(off)}$	Turn-Off Delay Time		-	136	282	ns
t_f	Turn-Off Fall Time		(Note 4)	-	113	236
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 48V, I_D = 80A$ $V_{GS} = 10V$	-	57	74	nC
Q_{gs}	Gate to Source Gate Charge		-	15	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	24	-

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	80	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	320	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 80A$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_{SD} = 80A$	-	64	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	127	-	nC

Notes:

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: $L = 0.15mH, I_{AS} = 80A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ C.$
- 3: $I_{SD} \leq 80A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}, \text{Starting } T_J = 25^\circ C.$
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

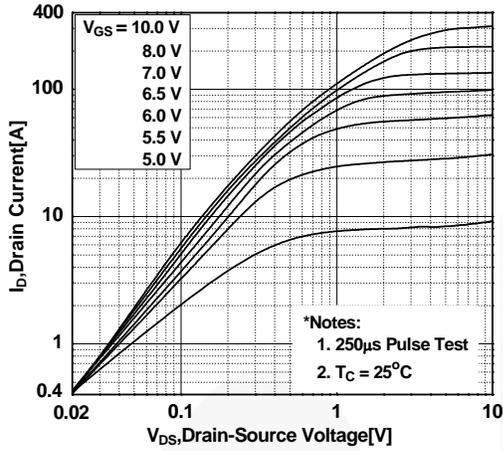


Figure 2. Transfer Characteristics

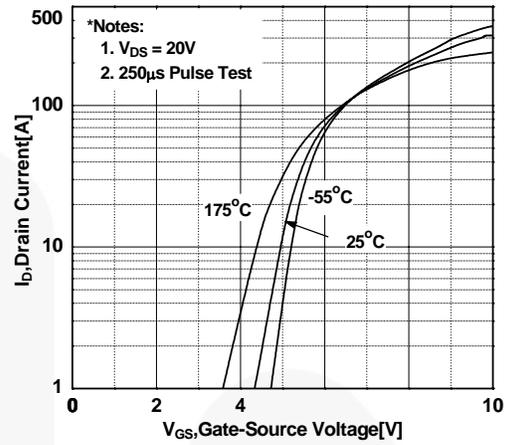


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

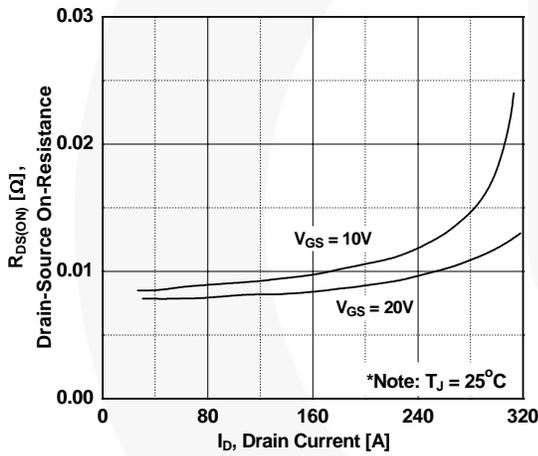


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

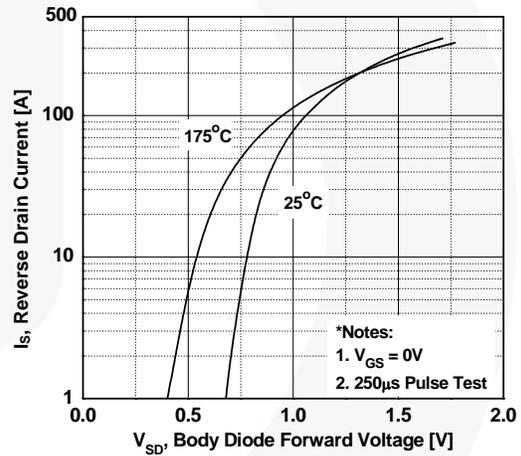


Figure 5. Capacitance Characteristics

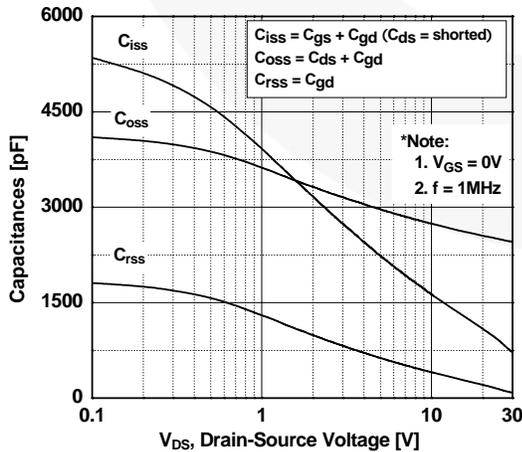
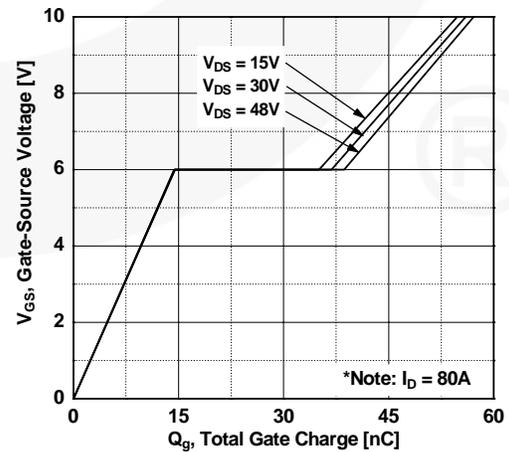


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

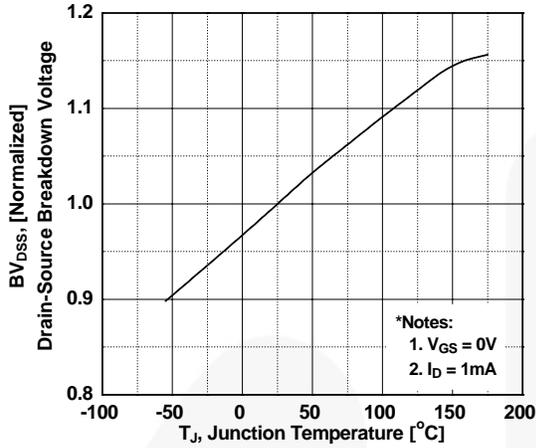


Figure 8. On-Resistance Variation vs. Temperature

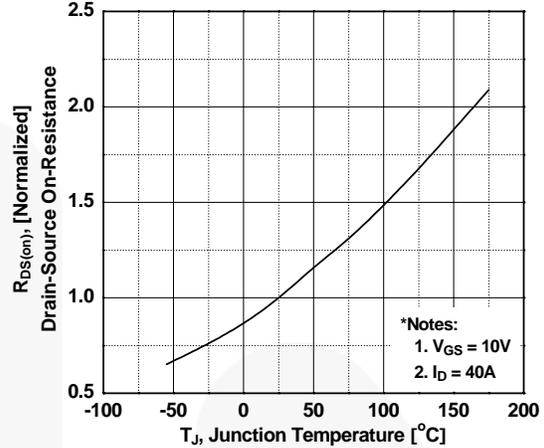


Figure 9. Maximum Safe Operating Area

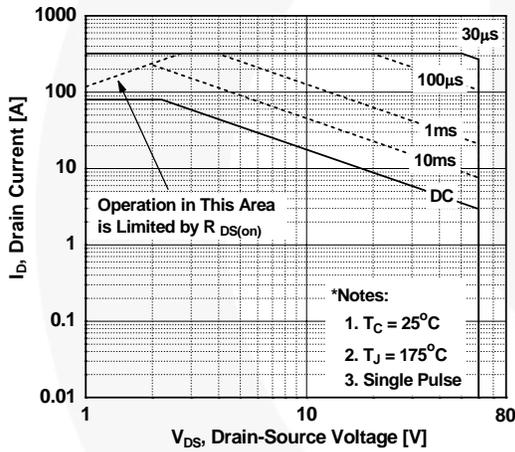


Figure 10. Maximum Drain Current vs. Case Temperature

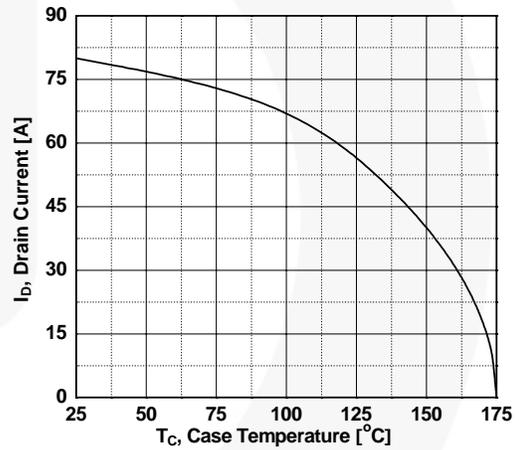


Figure 11. Transient Thermal Response Curve

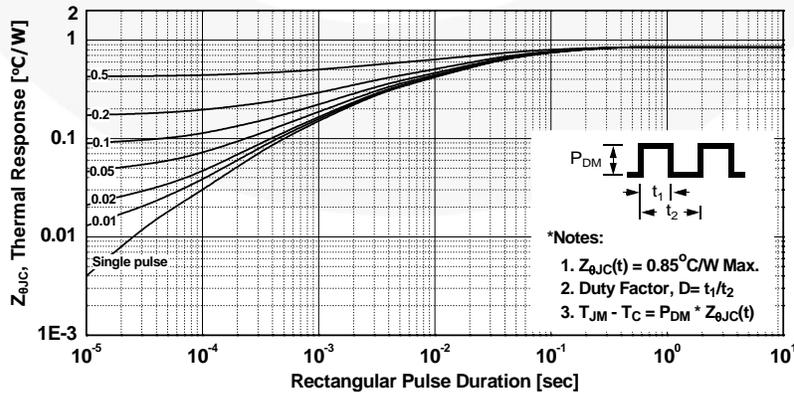


Figure 12. Gate Charge Test Circuit & Waveform

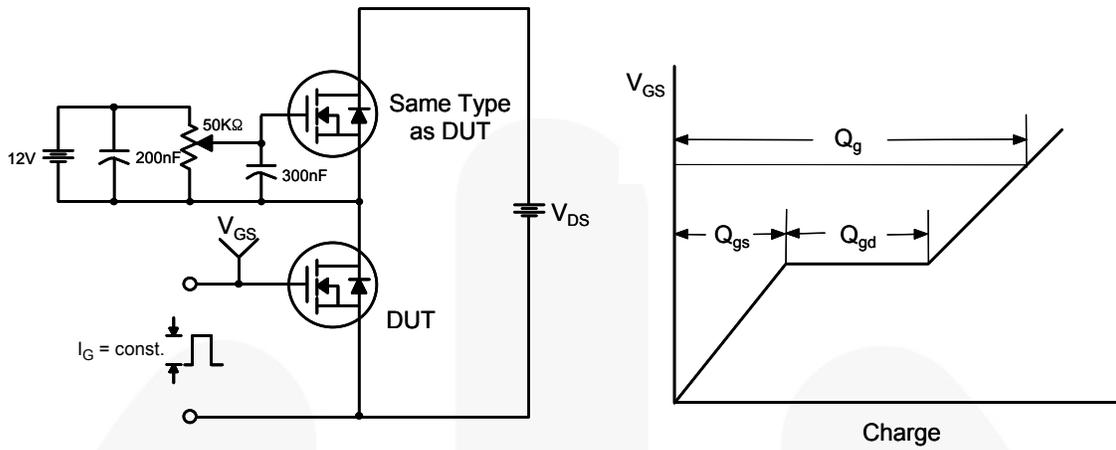


Figure 13. Resistive Switching Test Circuit & Waveforms

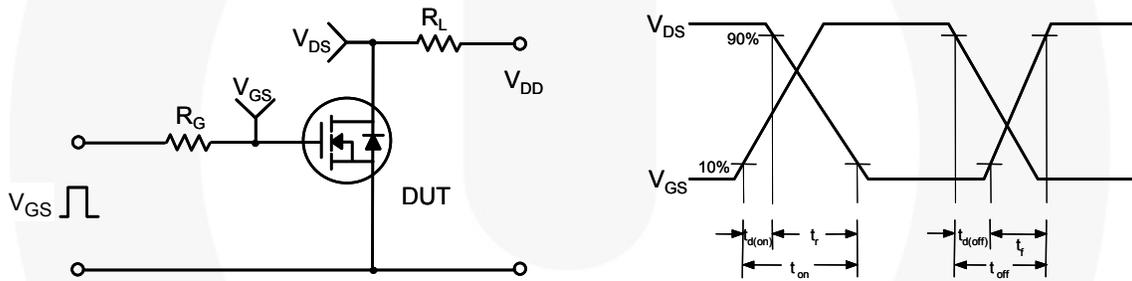


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

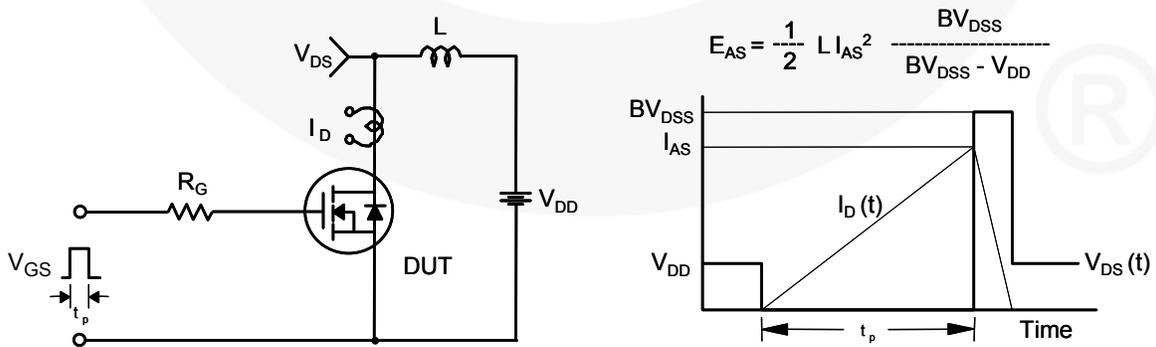
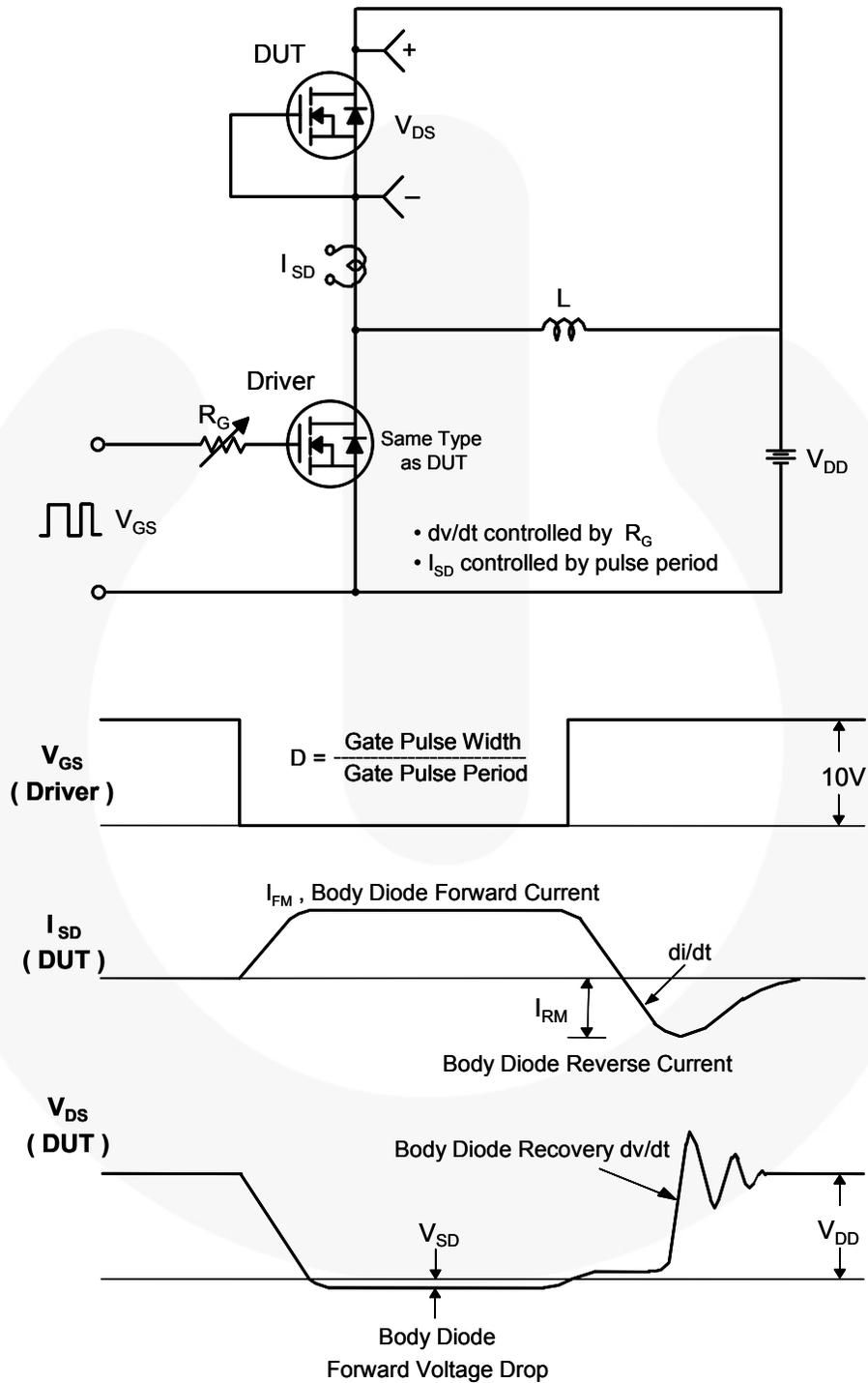


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

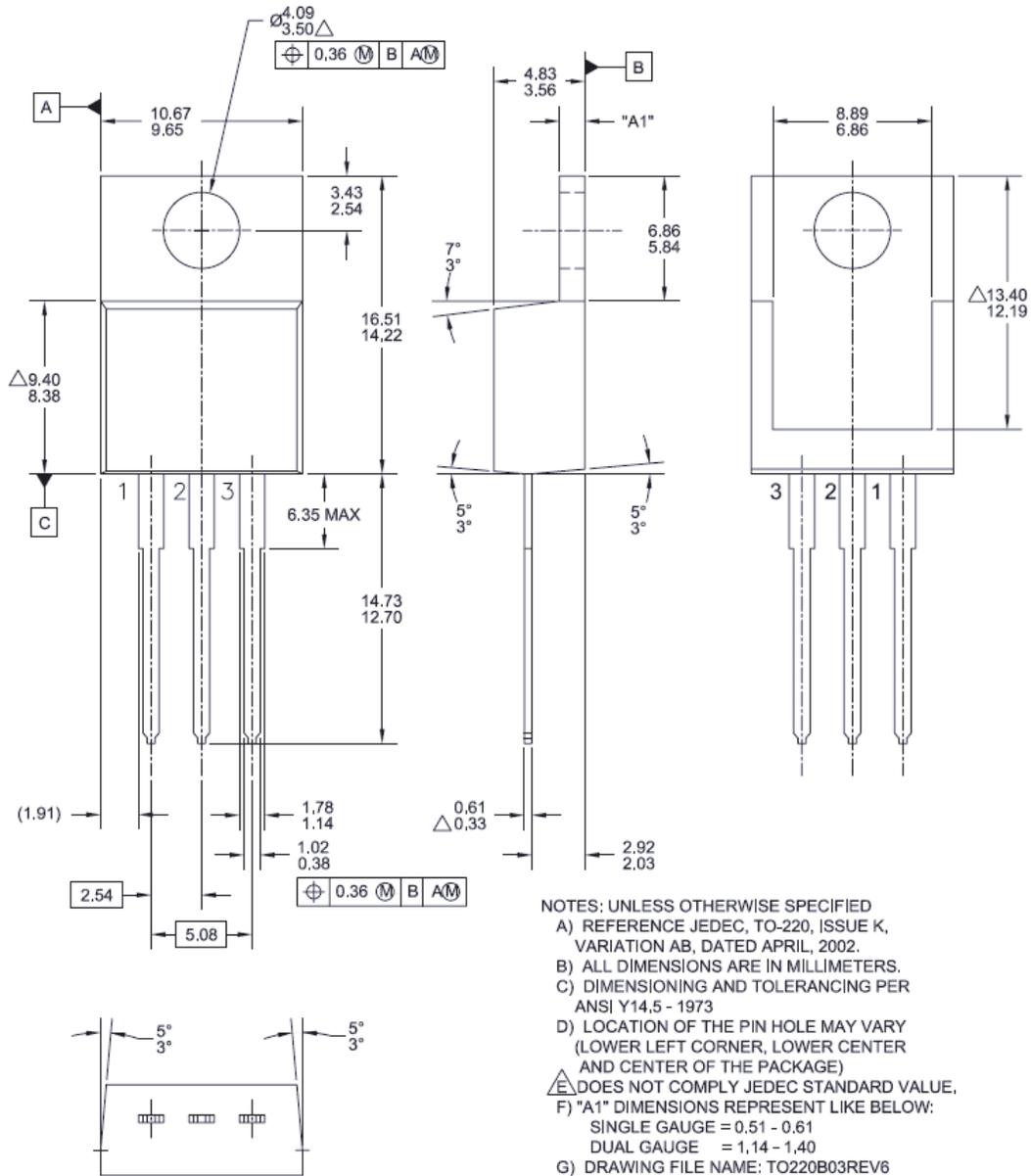


Figure 16. TO-220, Molded, 3Lead, Jedec Variation AB

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